ESD Protection Diode

Micro-Packaged Diodes for ESD Protection

ESD7381

The ESD7381 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Features

• Ultra-Low Capacitance: 0.37 pF

• Low Clamping Voltage

• Small Body Outline Dimensions: 0.60 mm x 0.30 mm

Low Body Height: 0.3 mmStand-off Voltage: 3.3 V

• Low Leakage

• Insertion Loss: 0.030 dBm

• Response Time is < 1 ns

• Low Dynamic Resistance $< 1 \Omega$

• IEC61000-4-2 Level 4 ESD Protection

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

• RF Signal ESD Protection

• RF Switching, PA, and Antenna ESD Protection

• Near Field Communications

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±20 ±20	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T _A = 25°C Thermal Resistance, Junction-to-Ambient	P _D R _{θJA}	250 400	mW °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-40 to +125	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.



ON Semiconductor®

www.onsemi.com





X3DFN2 CASE 152AF



PIN 1

ЕМ

E = Specific Device Code

M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7381MUT5G	X3DFN2 (Pb-Free)	10000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

See Application Note AND8308/D for further description of survivability specs.

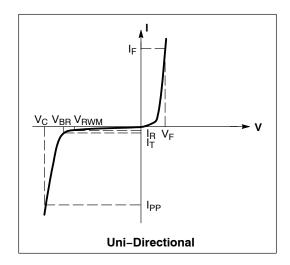
1

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
<u> </u>	
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}				3.3	V
Breakdown Voltage (Note 2)	V_{BR}	I _T = 1 mA	5.0			V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V		< 1.0	50	nA
Clamping Voltage (Note 3)	V _C	I _{PP} = 1 A			8.0	V
Clamping Voltage (Note 3)	V _C	I _{PP} = 3 A			10	V
ESD Clamping Voltage	V _C	Per IEC61000-4-2	See Figures 1 and 2			
Junction Capacitance C _J		V _R = 0 V, f = 1 Mhz V _R = 0 V, f < 1 GHz		0.37 0.25	0.55 0.55	pF
Dynamic Resistance	R _{DYN}	TLP Pulse		0.32		Ω
		f = 1 Mhz f = 8.5 GHz		0.030 0.573		dB

- 2. Breakdown voltage is tested from pin 1 to 2.
- 3. Non-repetitive current pulse at $T_A = 25$ °C, per IEC61000-4-5 waveform.

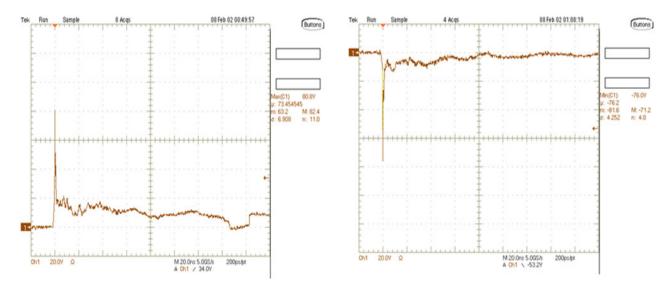
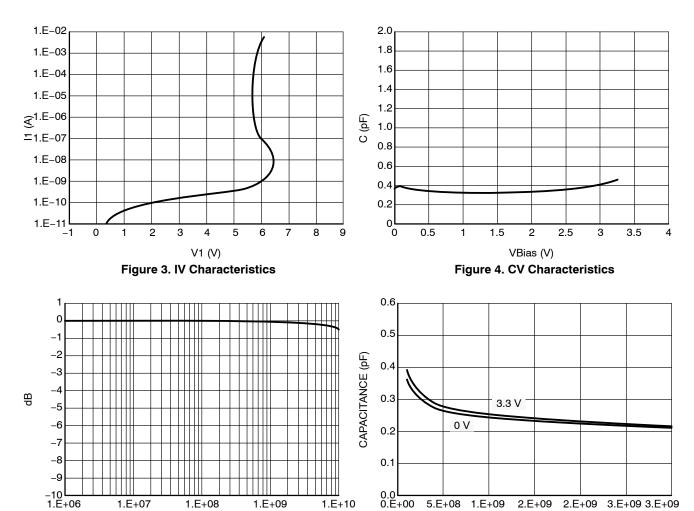


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

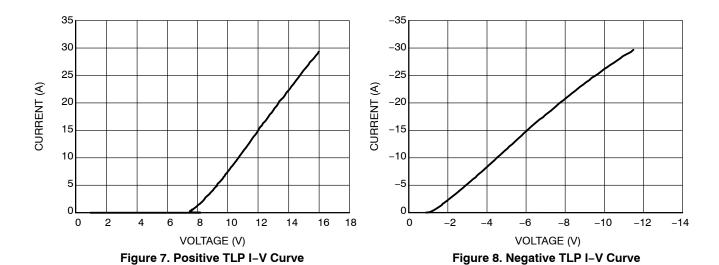
Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

ESD7381



FREQUENCY (Hz)
Figure 5. RF Insertion Loss

FREQUENCY
Figure 6. Capacitance over Frequency



IEC 61000-4-2 Spec.

	_			
Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

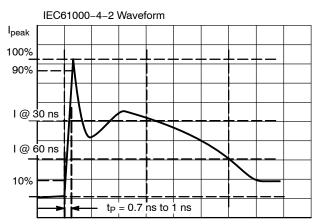


Figure 9. IEC61000-4-2 Spec

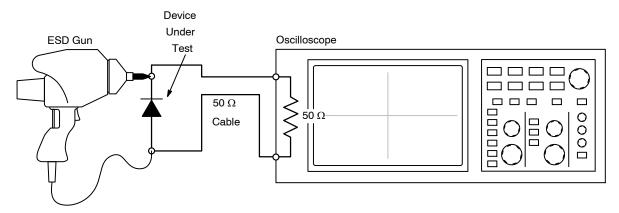


Figure 10. Diagram of ESD Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

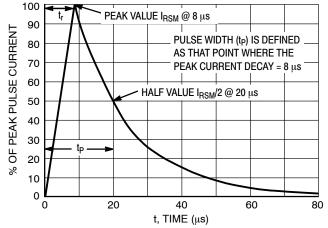
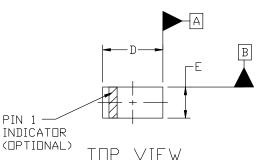


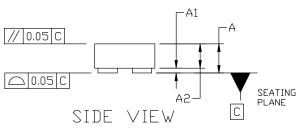
Figure 11. 8 X 20 μs Pulse Waveform

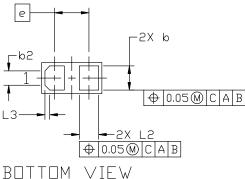


X3DFN2 0.62x0.32x0.24, 0.35P CASE 152AF ISSUE C

DATE 08 AUG 2023







GENERIC MARKING DIAGRAM*



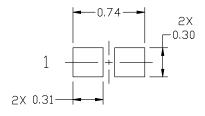
X = Specific Device Code

M = Date Code

NOTES:

- .. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 0201

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	0,25	0.29	0.33	
A1	0.00		0.05	
A2	0.14	0.24	0.34	
b	0.22	0.25	0.28	
b2	0.150 REF			
D	0.58	0.62	0.66	
E	0.28	0.32	0.36	
е	0.355 BSC			
L2	0.17	0.20	0.23	
L3	0.050 REF			



RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the □N Semiconductor Soldering and Mounting Techniques Reference Manual, S□LDERRM/D.

DOCUMENT NUMBER:	98AON56472E	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	X3DFN2 0.62x0.32x0.24, 0.35P		PAGE 1 OF 1	

onsemi and ONSemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

onsemi, ONSEMI., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems. or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales